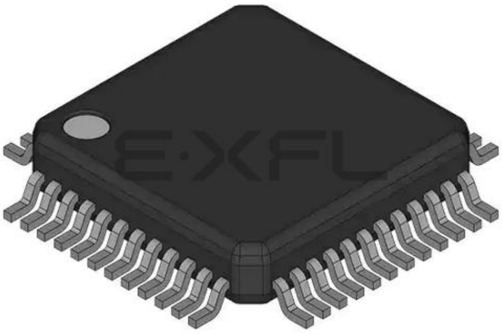
Freescale Semiconductor - MKV10Z16VLF7 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	75MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	DMA, WDT
Number of I/O	40
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mkv10z16vlf7

1 Ratings

1.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human-body model	-2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105 °C	-100	+100	mA	

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.

1.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	120	mA
V_{IO}	Digital pin input voltage (except open drain pins)	–0.3	VDD + 0.3[1]	V
	Open drain pins (PTC6 and PTC7)	–0.3	5.5	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V

1. Maximum value of V_{IO} (except open drain pins) must be 3.8 V.

2 General

Electromagnetic compatibility (EMC) performance depends on the environment in which the MCU resides. Board design and layout, circuit topology choices, location, characteristics of external components, and MCU software operation play a significant role in EMC performance.

See the following applications notes available on freescale.com for guidelines on optimizing EMC performance.

- *AN2321: Designing for Board Level Electromagnetic Compatibility*
- *AN1050: Designing for Electromagnetic Compatibility (EMC) with HCMOS Microcontrollers*
- *AN1263: Designing for Electromagnetic Compatibility with Single-Chip Microcontrollers*
- *AN2764: Improving the Transient Immunity Performance of Microcontroller-Based Applications*
- *AN1259: System Design and Layout Techniques for Noise Reduction in MCU-Based Systems*

2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
I_{ICcont}	Contiguous pin DC injection current—regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection	–25	—	mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	

1. All I/O pins are internally clamped to V_{SS} through an ESD protection diode. There is no diode connection to V_{DD}. If V_{IN} greater than V_{IO_MIN} (= V_{SS}-0.3 V) is observed, then there is no need to provide current limiting resistors at the pads. If this limit cannot be observed, then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R = (V_{IO\_MIN} - V_{IN})/I_{ICIO}$.

2.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling V_{DD} POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±60	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±40	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising thresholds are falling threshold + hysteresis voltage

- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

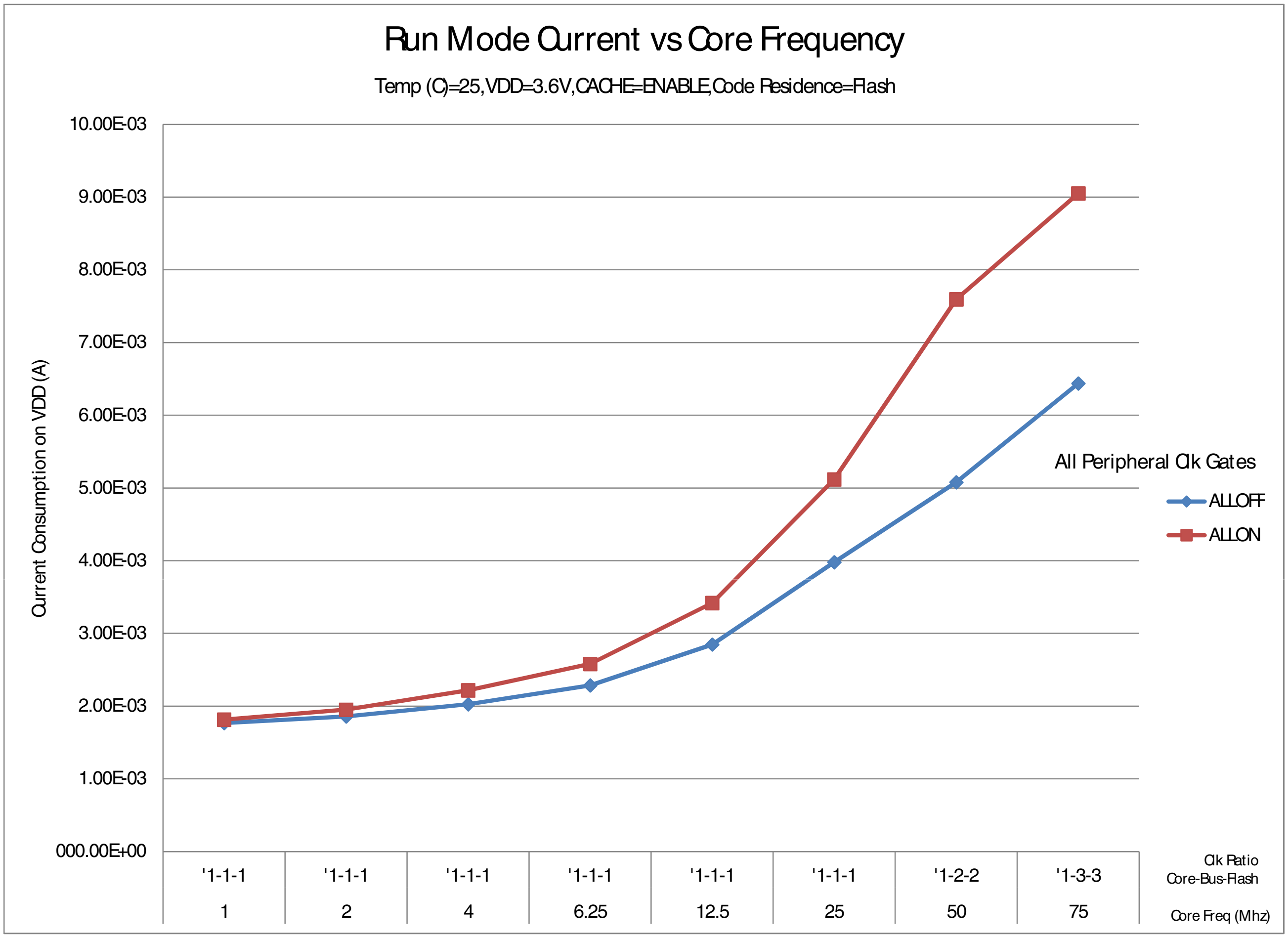

Figure 3. Run mode supply current vs. core frequency

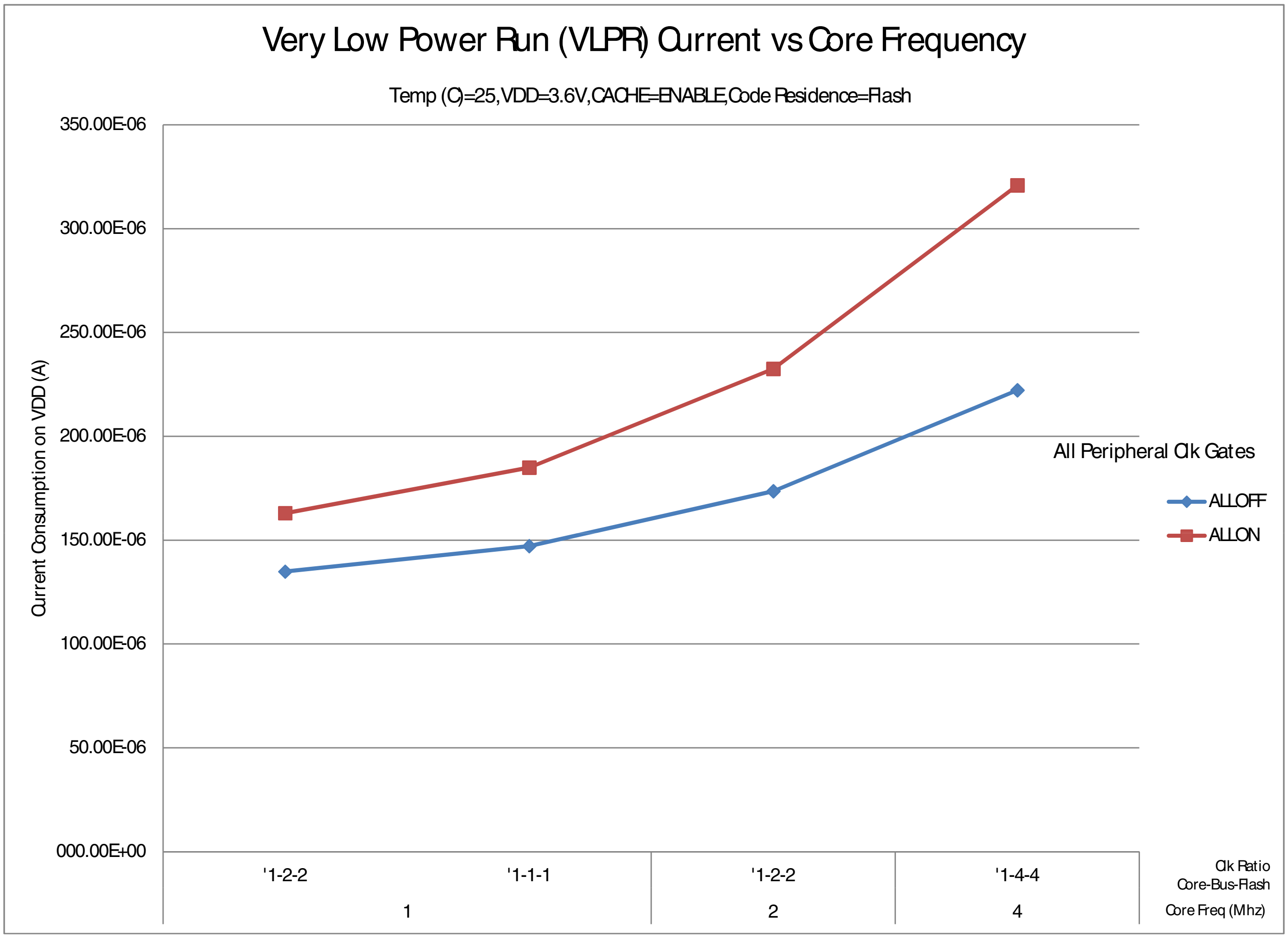

Figure 4. VLPR mode current vs. core frequency

2.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	15	dBμV	1, 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	17	dBμV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	12	dBμV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	4	dBμV	
V_{RE_IEC}	IEC level	0.15–1000	M	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code.

3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
4. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

3 Peripheral operating requirements and behaviors

3.1 Core modules

3.1.1 SWD Electricals

Table 13. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	SWD_CLK frequency of operation • Serial wire debug	0	25	MHz
J2	SWD_CLK cycle period	1/J1	—	ns
J3	SWD_CLK clock pulse width • Serial wire debug	20	—	ns
J4	SWD_CLK rise and fall times	—	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	—	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	—	ns
J11	SWD_CLK high to SWD_DIO data valid	—	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	—	ns

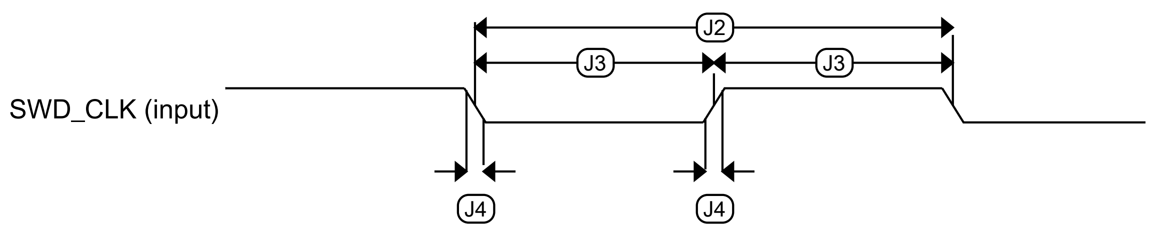

Figure 5. Serial wire clock input timing

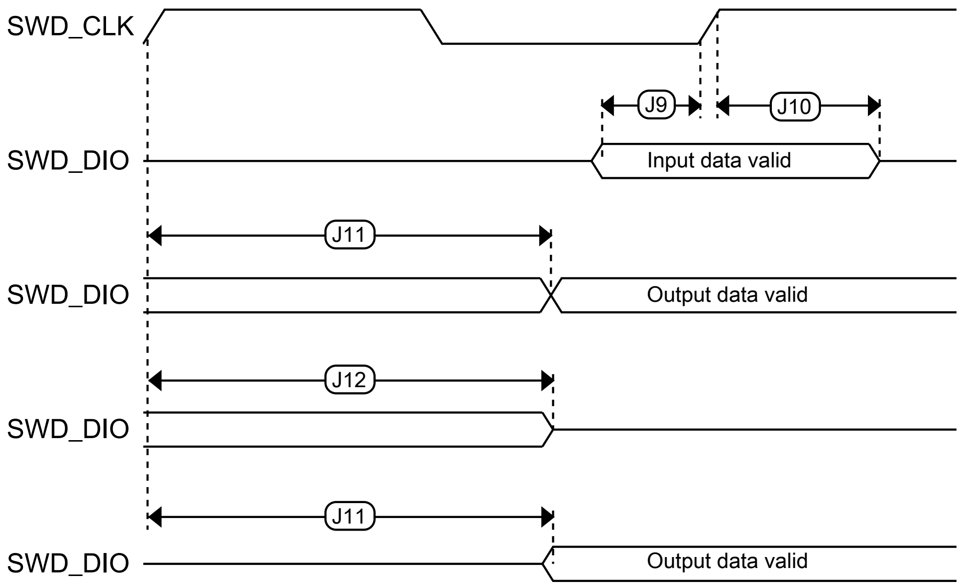

Figure 6. Serial wire data timing

3.2 System modules

There are no specifications necessary for the device's system modules.

3.3 Clock modules

3.3.1 MCG specifications

Table 14. MCG specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal V_{DD} and 25 °C	—	32.768	—	kHz	
f_{ints_t}	Internal reference frequency (slow clock) — user trimmed	31.25	—	39.0625	kHz	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM	—	± 0.3	± 0.6	$\%f_{dco}$	1

Table continues on the next page...

3.4.1.2 Flash timing specifications — commands

Table 18. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{pgmchk}	Program Check execution time	—	—	45	μs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	—
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—		ms	—
t_{rdonce}	Read Once execution time	—	—	25	μs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μs	—
t_{ersall}	Erase All Blocks execution time	—			ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

3.4.1.3 Flash high voltage current behaviors

Table 19. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 20. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	—
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	—
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at –40 °C ≤ T_j ≤ 125 °C.

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

3.6.1 ADC electrical specifications

3.6.1.1 16-bit ADC operating conditions

Table 21. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} ($V_{DD} – V_{DDA}$)	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} ($V_{SS} – V_{SSA}$)	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	
V_{ADIN}	Input voltage		V_{REFL}	—	V_{REFH}	V	
C_{ADIN}	Input capacitance	• 16-bit mode • 8-bit / 10-bit / 12-bit modes	— —	8 4	10 5	pF	
R_{ADIN}	Input resistance		—	2	5	kΩ	
R_{AS}	Analog source resistance	13-bit / 12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	3
f_{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	24.0	MHz	4
f_{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C_{rate}	ADC conversion rate	≤ 13-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	1200	Ksps	5
C_{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	Ksps	5

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

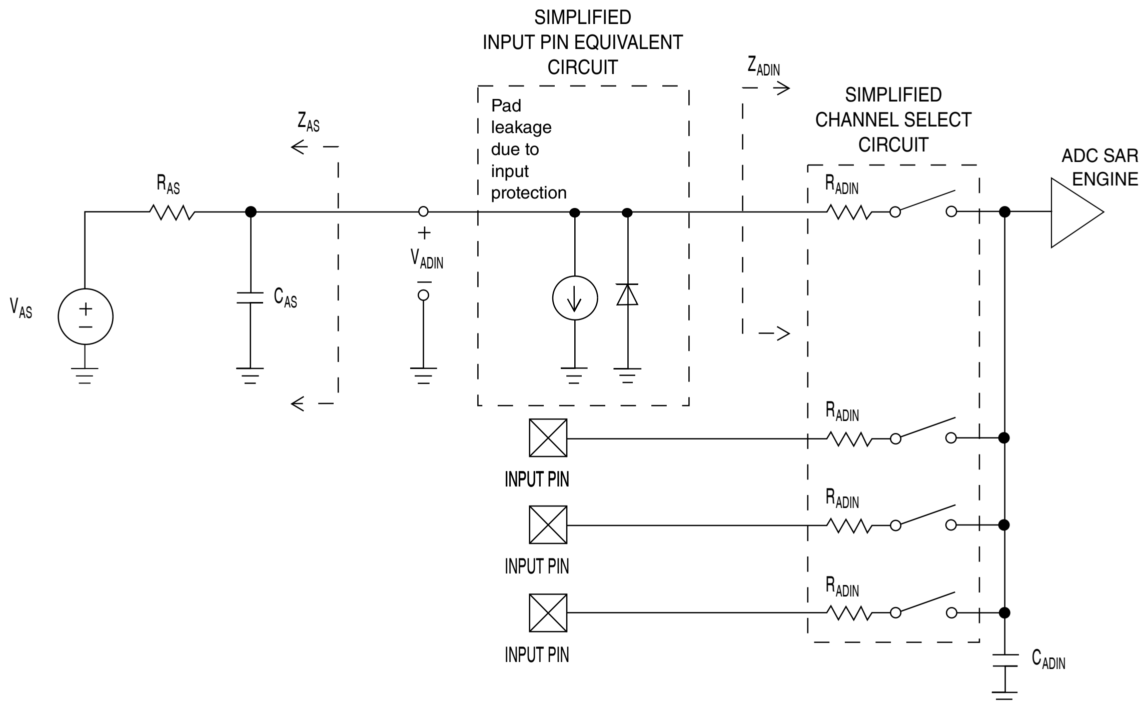

Figure 7. ADC input impedance equivalency diagram

3.6.1.2 16-bit ADC electrical characteristics

Table 22. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions[1].	Min.	Typ.[2]	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0 • ADLPC = 1, ADHSC = 1 • ADLPC = 0, ADHSC = 0 • ADLPC = 0, ADHSC = 1	1.2 2.4 3.0 4.4	2.4 4.0 5.2 6.2	3.9 6.1 7.3 9.5	MHz MHz MHz MHz	$t_{ADACK} = 1/f_{ADACK}$
	Sample Time	See Reference Manual chapter for sample times					

Table continues on the next page...

Table 22. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions[1].	Min.	Typ.[2]	Max.	Unit	Notes
TUE	Total unadjusted error	• 12-bit modes • <12-bit modes	— —	±4 ±1.4	±6.8 ±2.1	LSB[4]	5
DNL	Differential non-linearity	• 12-bit modes • <12-bit modes	— —	±0.7 ±0.2	–1.1 to +1.9 –0.3 to 0.5	LSB[4]	5
INL	Integral non-linearity	• 12-bit modes • <12-bit modes	— —	±1.0 ±0.5	–2.7 to +1.9 –0.7 to +0.5	LSB[4]	5
E_{FS}	Full-scale error	• 12-bit modes • <12-bit modes	— —	–4 –1.4	–5.4 –1.8	LSB[4]	$V_{ADIN} = V_{DDA}$[5]
E_Q	Quantization error	• 16-bit modes • ≤13-bit modes	— —	–1 to 0 —	— ±0.5	LSB[4]	
ENOB	Effective number of bits	16-bit differential mode • Avg = 32 • Avg = 4 16-bit single-ended mode • Avg = 32 • Avg = 4	12.8 11.9 12.2 11.4	14.5 13.8 13.7 13.1	— — — —	bits bits bits bits	6
SINAD	Signal-to-noise plus distortion	See ENOB	6.02 × ENOB + 1.76			dB	
THD	Total harmonic distortion	16-bit differential mode • Avg = 32 16-bit single-ended mode • Avg = 32	— —	–97 –91	— —	dB dB	7
SFDR	Spurious free dynamic range	16-bit differential mode • Avg = 32 16-bit single-ended mode • Avg = 32	82 78	100 92	— —	dB dB	7
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage

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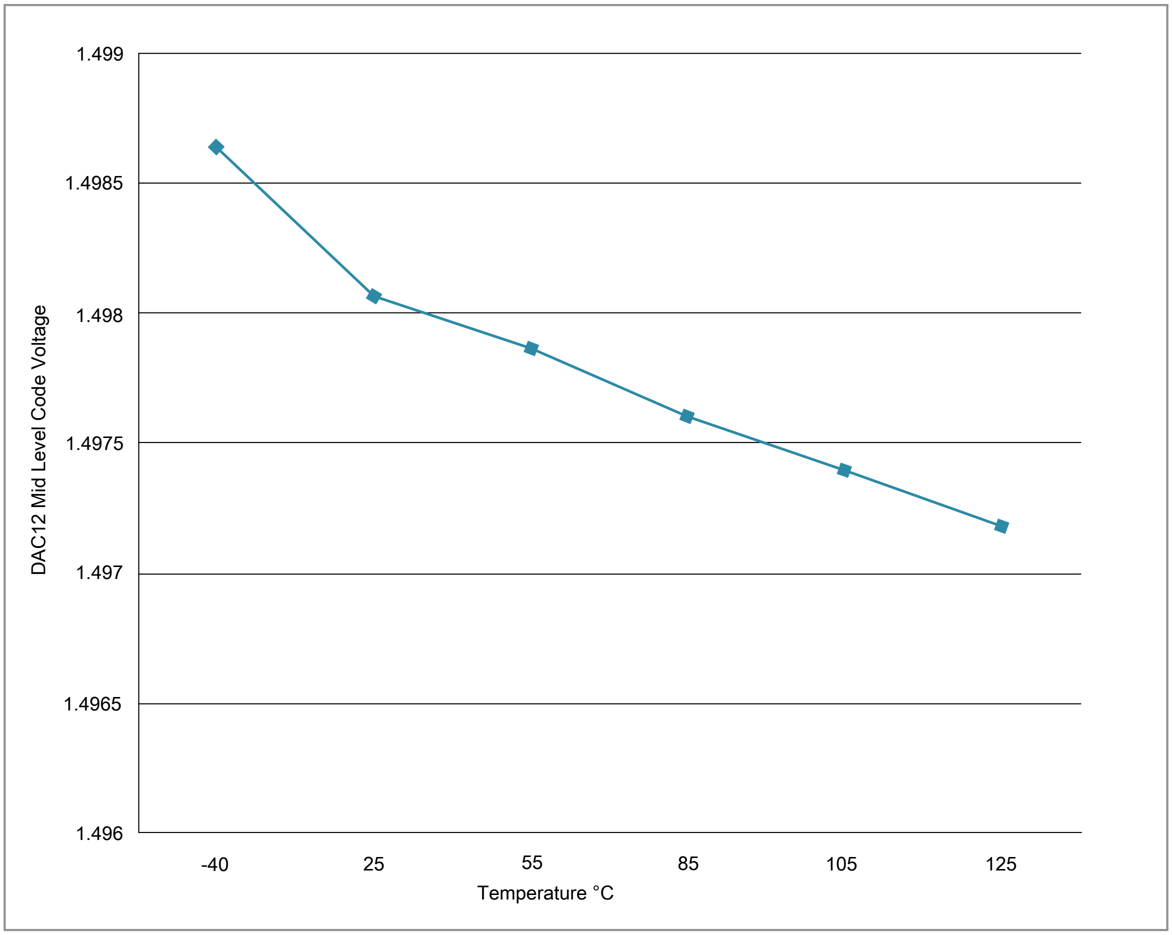


Figure 13. Offset at half scale vs. temperature

3.7 Timers

See General switching specifications.

3.8 Communication interfaces

3.8.1 DSPI switching specifications (limited voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 26. Master mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	25	MHz	
DS1	DSPI_SCK output cycle time	2 x t_{BUS}	—	ns	
DS2	DSPI_SCK output high/low time	$(t_{SCK}/2) - 2$	$(t_{SCK}/2) + 2$	ns	
DS3	DSPI_PCS*n* valid to DSPI_SCK delay	$(t_{BUS} \times 2) - 2$	—	ns	1
DS4	DSPI_SCK to DSPI_PCS*n* invalid delay	$(t_{BUS} \times 2) - 2$	—	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	—	8.5	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	–2	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	17	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
2. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

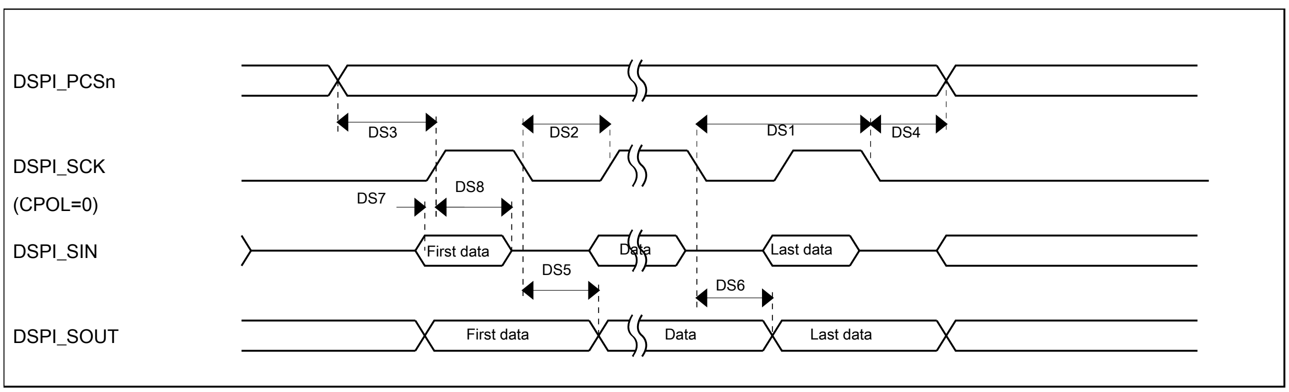


Figure 14. DSPI classic SPI timing — master mode

Table 27. Slave mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
	Frequency of operation		12.5	MHz

Table continues on the next page...

Table 28. Master mode DSPI timing (full voltage range) (continued)

Num	Description	Min.	Max.	Unit	Notes
DS3	DSPI_PCS*n* valid to DSPI_SCK delay	(t_{BUS} x 2) – 4	—	ns	2
DS4	DSPI_SCK to DSPI_PCS*n* invalid delay	(t_{BUS} x 2) – 4	—	ns	3
DS5	DSPI_SCK to DSPI_SOUT valid	—	10	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	–7.8	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	24	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The DSPI module can operate across the entire operating voltage for the processor, but to run across the full voltage range the maximum frequency of operation is reduced.
2. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
3. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

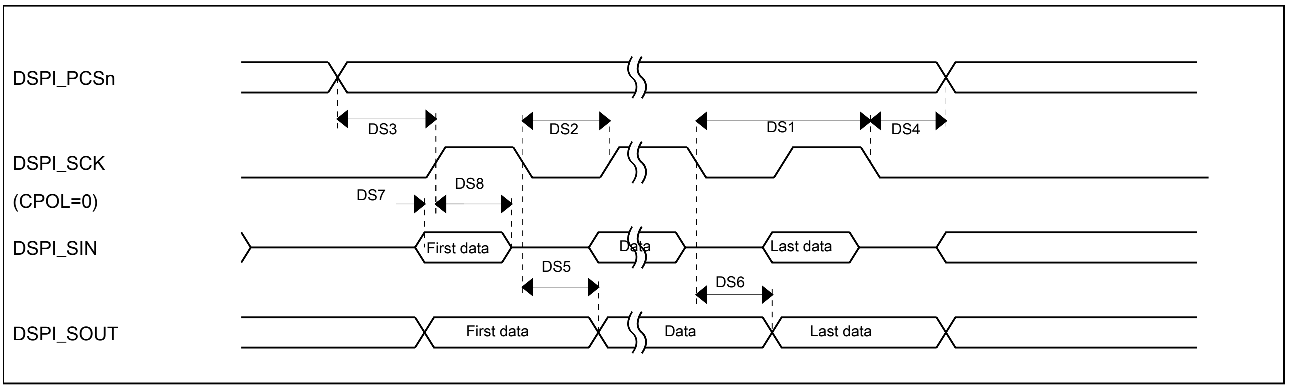


Figure 16. DSPI classic SPI timing — master mode

Table 29. Slave mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
	Frequency of operation	—	6.25	MHz
DS9	DSPI_SCK input cycle time	8 x t_{BUS}	—	ns
DS10	DSPI_SCK input high/low time	(t_{SCK}/2) - 4	($t_{SCK/2)}$ + 4	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	27.5	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2.5	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	22	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	22	ns

48 LQFP	32 QFN	32 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
15	10	10	PTE24	DISABLED		PTE24		FTM0_CH0		I2C0_SCL	EWM_OUT_b	
16	11	11	PTE25	DISABLED		PTE25		FTM0_CH1		I2C0_SDA	EWM_IN	
17	12	12	PTA0	SWD_CLK		PTA0	UART0_ CTS_b	FTM0_CH5				SWD_CLK
18	13	13	PTA1	DISABLED		PTA1	UART0_RX	FTM2_CH0	CMP0_OUT	FTM2_QD_ PHA	FTM1_CH1	
19	14	14	PTA2	DISABLED		PTA2	UART0_TX	FTM2_CH1	CMP1_OUT	FTM2_QD_ PHB	FTM1_CH0	
20	15	15	PTA3	SWD_DIO		PTA3	UART0_ RTS_b	FTM0_CH0	FTM2_FLT0	EWM_OUT_b		SWD_DIO
21	16	16	PTA4	NMI_b		PTA4/ LLWU_P3		FTM0_CH1		FTM0_FLT3		NMI_b
22	—	—	VDD	VDD	VDD							
23	—	—	VSS	VSS	VSS							
24	17	17	PTA18	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_CLKIN0			
25	18	18	PTA19	XTAL0	XTAL0	PTA19	FTM0_FLT0	FTM1_FLT0	FTM_CLKIN1		LPTMR0_ ALT1	
26	19	19	PTA20	RESET_b		PTA20						RESET_b
27	20	20	PTB0	ADC0_SE8/ ADC1_SE8	ADC0_SE8/ ADC1_SE8	PTB0/ LLWU_P5	I2C0_SCL	FTM1_CH0			FTM1_QD_ PHA	UART0_RX
28	21	21	PTB1	ADC0_SE9/ ADC1_SE9	ADC0_SE9/ ADC1_SE9	PTB1	I2C0_SDA	FTM1_CH1	FTM0_FLT2	EWM_IN	FTM1_QD_ PHB	UART0_TX
29	—	—	PTB2	ADC0_SE10/ ADC1_SE10/ ADC1_DM2	ADC0_SE10/ ADC1_SE10/ ADC1_DM2	PTB2	I2C0_SCL	UART0_ RTS_b	FTM0_FLT1		FTM0_FLT3	
30	—	—	PTB3	ADC1_SE2/ ADC1_DP2	ADC1_SE2/ ADC1_DP2	PTB3	I2C0_SDA	UART0_ CTS_b			FTM0_FLT0	
31	—	—	PTB16	DISABLED		PTB16		UART0_RX	FTM_CLKIN2		EWM_IN	
32	—	—	PTB17	DISABLED		PTB17		UART0_TX	FTM_CLKIN1		EWM_OUT_b	
33	—	—	PTC0	ADC1_SE11	ADC1_SE11	PTC0	SPI0_PCS4	PDB0_ EXTRG		CMP0_OUT	FTM0_FLT0	SPI0_PCS0/ SS_b
34	22	22	PTC1	ADC1_SE3	ADC1_SE3	PTC1/ LLWU_P6	SPI0_PCS3	UART1_ RTS_b	FTM0_CH0	FTM2_CH0		
35	23	23	PTC2	ADC0_SE11/ CMP1_IN0	ADC0_SE11/ CMP1_IN0	PTC2	SPI0_PCS2	UART1_ CTS_b	FTM0_CH1	FTM2_CH1		
36	24	24	PTC3	CMP1_IN1	CMP1_IN1	PTC3/ LLWU_P7	SPI0_PCS1	UART1_RX	FTM0_CH2	CLKOUT		
37	25	25	PTC4	DISABLED		PTC4/ LLWU_P8	SPI0_PCS0/ SS_b	UART1_TX	FTM0_CH3		CMP1_OUT	
38	26	26	PTC5	DISABLED		PTC5/ LLWU_P9	SPI0_SCK	LPTMR0_ ALT2			CMP0_OUT	FTM0_CH2
39	27	27	PTC6	CMP0_IN0	CMP0_IN0	PTC6/ LLWU_P10	SPI0_SOUT	PDB0_ EXTRG		UART0_RX		I2C0_SCL
40	28	28	PTC7	CMP0_IN1	CMP0_IN1	PTC7	SPI0_SIN			UART0_TX		I2C0_SDA

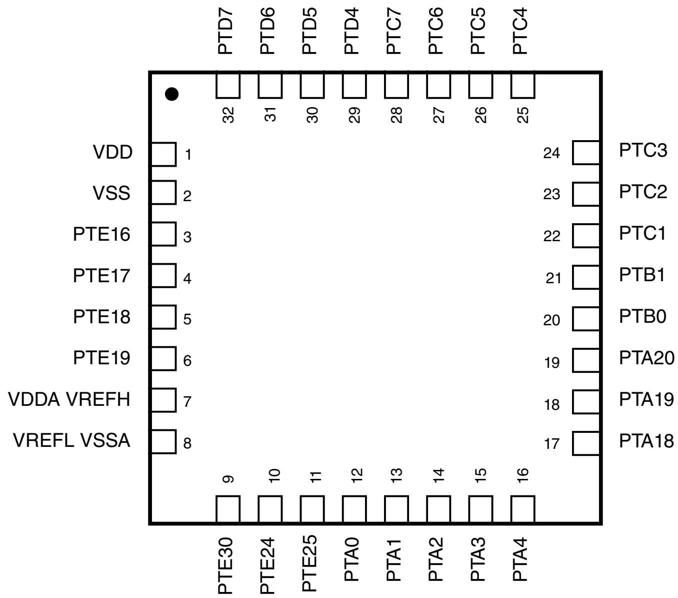


Figure 19. 32 QFN Pinout Diagram

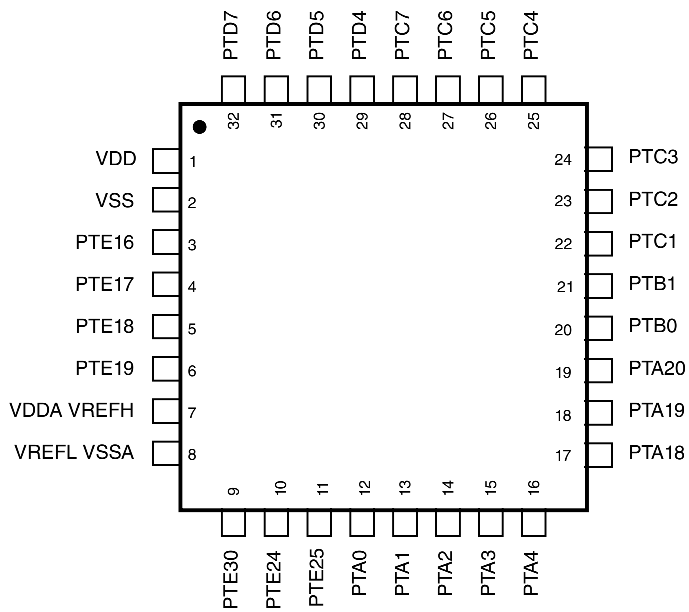


Figure 20. 32 LQFP Pinout Diagram

6 Ordering parts

6.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to www.freescale.com and perform a part number search for the MKV10 device numbers.

7 Part identification

7.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

7.2 Format

Part numbers for this device have the following format:

Q KV## A FFF R T PP CC N

7.3 Fields

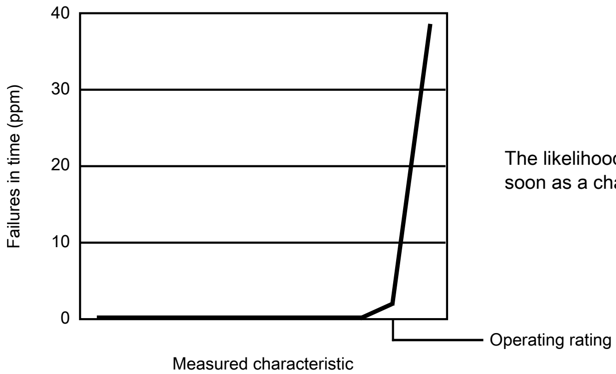
This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
KV##	Kinetis family	• KV10
M	Key attribute	• Z = M0+ core
FFF	Program flash memory size	• 32 = 32 KB
T	Temperature range (°C)	• V = –40 to 105
PP	Package identifier	• FK = 24 QFN (4 mm x 4 mm) • LC = 32 LQFP (7 mm x 7 mm) • FM = 32 QFN (5 mm x 5 mm) • LF = 48 LQFP (7 mm x 7 mm) • FT = 48 QFN (10 mm x 10 mm) • LH = 64 LQFP (10 mm x 10 mm) • LK = 80 LQFP (12 mm x 12 mm) • LL = 100 LQFP (14 mm x 14 mm)
CCC	Maximum CPU frequency (MHz)	• 7 = 75 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

7.4 Example

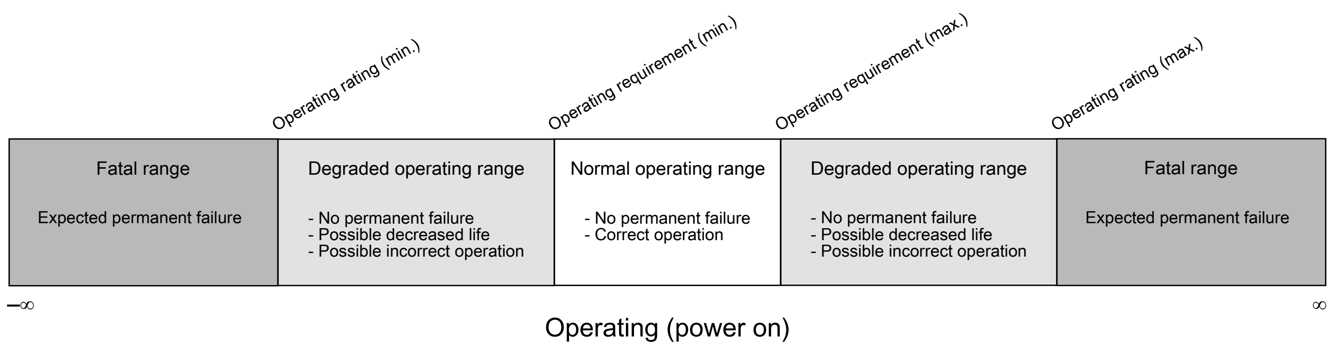
This is an example part number:

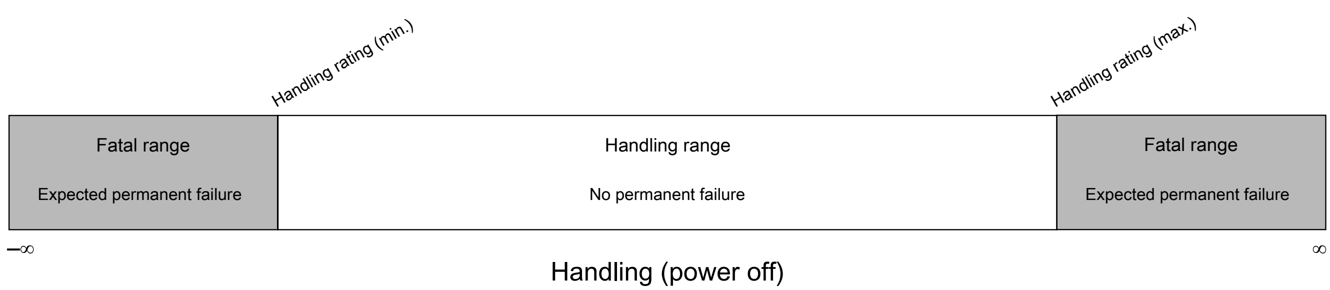
8.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

8.6 Relationship between ratings and operating requirements

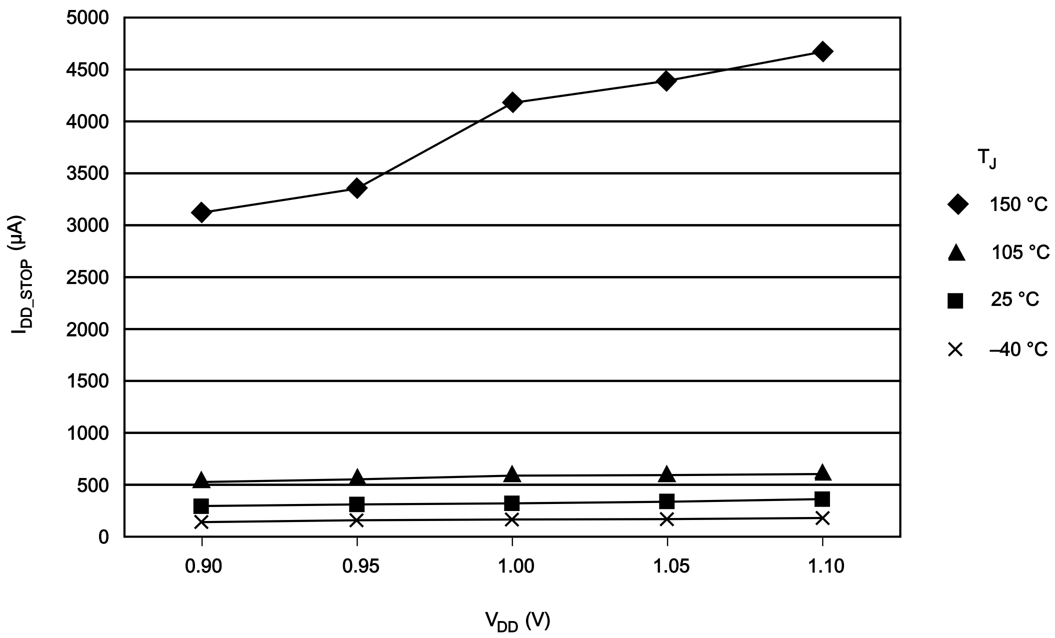




8.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.



8.9 Typical Value Conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

9 Revision history

The following table provides a revision history for this document.

Table 30. Revision history

Rev. No.	Date	Substantial Changes
3	02/2014	Initial public release
4	02/2015	• Updated the section "Power consumption operating behaviors" • Added a note below the "Thermal operating requirements" table.